

Silicon NPN Power Transistors

2SD1562 2SD1562A

DESCRIPTION

- With TO-220C package
- Complement to type 2SB1085/1085A
- High transition frequency

APPLICATIONS

- For low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

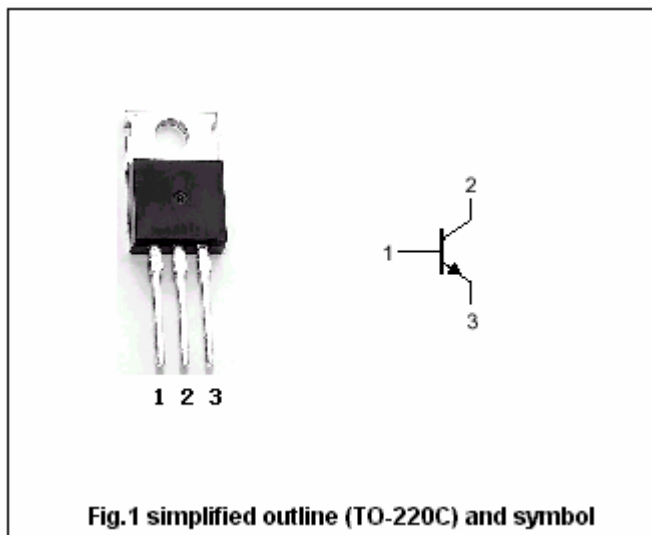


Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Tc=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SD1562	120	V
		2SD1562A	160	
V _{CEO}	Collector-emitter voltage	2SD1562	120	V
		2SD1562A	160	
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		1.5	A
I _{CM}	Collector current-peak		3.0	A
P _C	Collector power dissipation	T _C =25°C	20	W
		T _a =25°C	1.5	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SD1562	I _C =1mA; I _B =0	120			V
		2SD1562A		160			
V _{(BR)CBO}	Collector-base breakdown voltage	2SD1562	I _C =50μA; I _E =0	120			V
		2SD1562A		160			
V _{(BR)EBO}	Emitter-base breakdown voltage		I _E =50μA; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage		I _C =1 A; I _B =0.1 A			2.0	V
V _{BEsat}	Base-emitter on saturation voltage		I _C =1 A; I _B =0.1 A			1.5	V
I _{CBO}	Collector cut-off current		V _{CB} =120V; I _E =0			1.0	μA
I _{EBO}	Emitter cut-off current		V _{EB} =4V; I _C =0			1.0	μA
h _{FE}	DC current gain	2SD1562	I _C =0.1A; V _{CE} =5V	60		320	
		2SD1562A		60	200		
f _T	Transition frequency		I _E =-0.1A; V _{CE} =5V		80		MHz
C _{OB}	Output capacitance		I _E =0; V _{CB} =10V; f=1MHz		20		pF

◆ h_{FE} classifications

TYPE	D	E	F
2SD1562	60-120	100-200	160-320
2SD1562A	60-120	100-200	

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PACKAGE OUTLINE

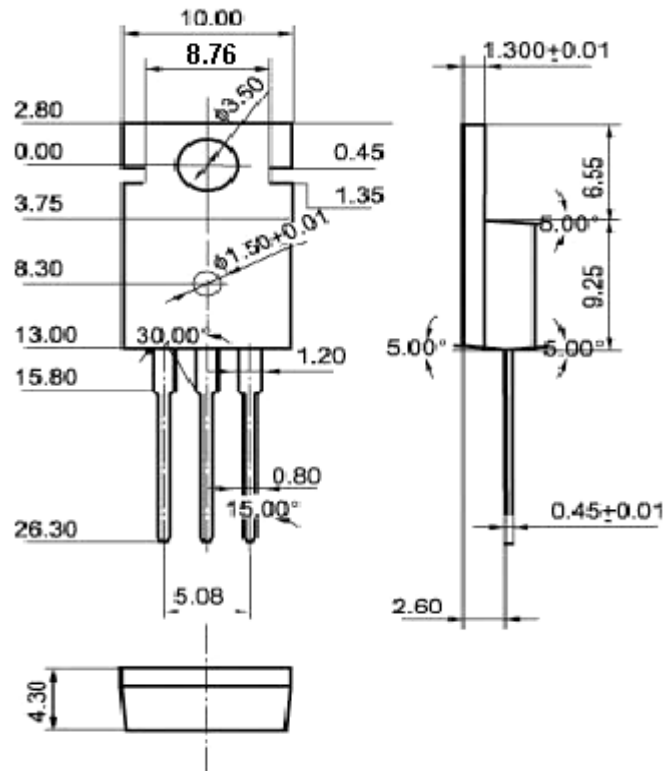


Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)